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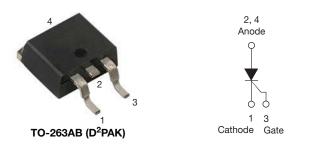
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Thyristor Surface Mount Phase Control SCR, 16 A



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PRODUCT SUMMARY								
Package	TO-263AB (D ² PAK)							
Diode variation	Single SCR							
I _{T(AV)}	10 A							
V _{DRM} /V _{RRM}	1600 V							
V _{TM}	1.4 V							
I _{GT}	60 mA							
TJ	-40 °C to 125 °C							

FEATURES

• Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



- Designed and qualified according JEDEC[®]-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are in identical package outlines

DESCRIPTION

The VS-16TTS16SPbF high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS	SINGLE-PHASE BRIDGE	UNITS						
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 μm) copper	2.5	3.5						
Aluminum IMS, R _{thCA} = 15 °C/W	6.3	9.5	A					
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	14.0	18.5						

Note

• $T_A = 55 \ ^\circ C$, $T_J = 125 \ ^\circ C$, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS									
SYMBOL	CHARACTERISTICS	VALUES	UNITS						
I _{T(AV)}	Sinusoidal waveform	10	•						
I _{RMS}		16	A						
V _{RRM} /V _{DRM}		1600	V						
I _{TSM}		200	A						
V _T	10 A, T _J = 25 °C	1.4	V						
dV/dt		500	V/µs						
dl/dt		150	A/µs						
TJ		-40 to 125	°C						

VOLTAGE RATINGS									
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA						
VS-16TTS16SPbF	1600	1600	10						



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ABSOLUTE MAXIMUM RATINGS	1						
PARAMETER	SYMBOL		TEST CONDITIONS	VAL			
PARAMETER	STIVIDUL		TEST CONDITIONS	TYP.	MAX.	UNITS	
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 18	0° conduction, half sine wave	1	0		
Maximum RMS on-state current	I _{RMS}			1	6	А	
Maximum peak, one-cycle,	I	10 ms sine pu	lse, rated V _{RRM} applied	17	70	A	
non-repetitive surge current	I _{TSM}	10 ms sine pu	lse, no voltage reapplied	20	00	1	
Maximum I ² t for fusing	l ² t	10 ms sine pu	10 ms sine pulse, rated V _{RRM} applied			A ² s	
Maximum - t for fusing	1-1	10 ms sine pu	lse, no voltage reapplied	200		A-S	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms to 1	t = 0.1 ms to 10 ms, no voltage reapplied				
Maximum on-state voltage drop	V_{TM}	10 A, T _J = 25 °	°C	1.4		V	
On-state slope resistance	r _t	T 105 °C		24.0		mΩ	
Threshold voltage	V _{T(TO)}	1J=125 C	T _J = 125 °C		.1	V	
Maximum reverse and direct leakage current	1 /1	T _J = 25 °C		0	.5		
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	$V_{R} = Rated V_{RRM}/V_{DRM}$	10		1	
Holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C			150	mA	
Maximum latching current	١L	Anode supply = 6 V, resistive load, T_J = 25 °C			00		
Maximum rate of rise of off-state voltage	dV/dt	T _J = T _J max. li	$T_J = T_J$ max. linear to 80 % $V_{DRM} = Rg - k = Open$			V/µs	
Maximum rate of rise of turned-on current	dl/dt			150		A∕µs	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	W	
Maximum average gate power	P _{G(AV)}		2.0	vv	
Maximum peak positive gate current	+ I _{GM}		1.5	А	
Maximum peak negative gate voltage	- V _{GM}		10	V	
		Anode supply = 6 V, resistive load, T_J = - 10 °C	90	mA	
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$	60		
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	35		
		Anode supply = 6 V, resistive load, T_J = - 10 °C	3.0		
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	2.0	N/	
voltage to trigger		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	1.0	V	
Maximum DC gate voltage not to trigger	V _{GD}		0.25		
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	2.0	mA	

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9					
Typical reverse recovery time	t _{rr}	T 105 %	4	μs				
Typical turn-off time	tq	T _J = 125 °C	110					

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THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL TEST CONDITIONS		VALUES	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		- 40 to 125				
Soldering temperature	Ts	For 10 s (1.6 mm from case)	260				
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.3	°C/W			
Typical thermal resistance, junction to ambient	R _{thJA}	PCB mount ⁽¹⁾	40	C/VV			
Approximate weight			2	g			
Approximate weight			0.07	oz.			
Marking device		Case style D ² PAK (SMD-220)	16TTS	16S			

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W.

For recommended footprint and soldering techniques refer to application note #AN-994.

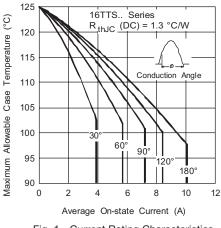


Fig. 1 - Current Rating Characteristics

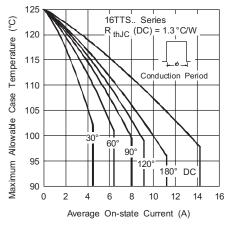


Fig. 2 - Current Rating Characteristics

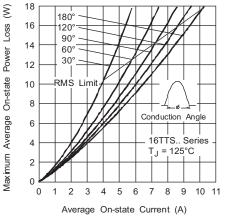


Fig. 3 - On-State Power Loss Characteristics

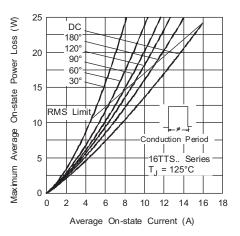


Fig. 4 - On-State Power Loss Characteristics

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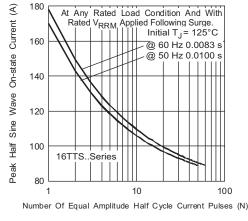
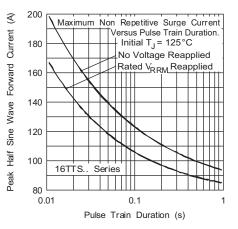
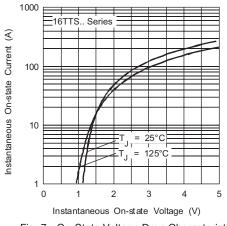


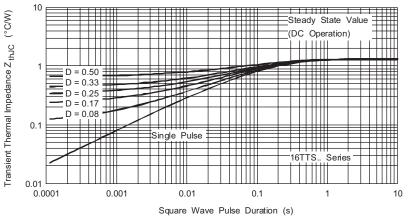
Fig. 5 - Maximum Non-Repetitive Surge Current





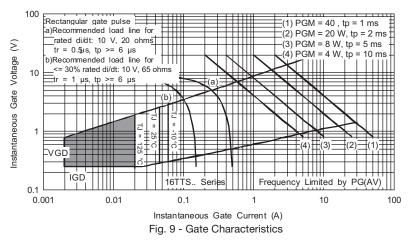








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ORDERING INFORMATION TABLE

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Device code	VS-	16	т	т	S	16	S	TRL	PbF		
		2	3	4	5	6	7	8	9		
	1	- Visł	nay Sem	niconduc	ctors pro	oduct					
	2	- Current rating									
	3	- Circ	Circuit configuration:								
		T =	T = single thyristor								
	4	- Pac	kage:								
		T =	TO-220	AC							
	5	- Тур	e of silio	con:							
		S =	standar	d recov	ery recti	ifier					
	6	- Voli	tage rati	ng: Volt	age cod	e x 100	= V _{RRI}	₄ (16 = ⁻	1600 V)		
	7	- S=	TO-220	D ² PAK	(SMD-	220) ve	rsion				
	8	- • No	one = tu	be							
		• TF	RL = tap	e and re	el (left d	oriented)				
		• TF	RR = tap	e and re	eel (righ	t oriente	ed)				
	9	- PbF	= lead	(Pb)-fre	е						

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-16TTS16SPbF	50	1000	Antistatic plastic tubes						
VS-16TTS16STRRPbF	800	800	13" diameter reel						
VS-16TTS16STRLPbF	800	800	13" diameter reel						

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95046						
Part marking information	www.vishay.com/doc?95054						
Packaging information	www.vishay.com/doc?95032						

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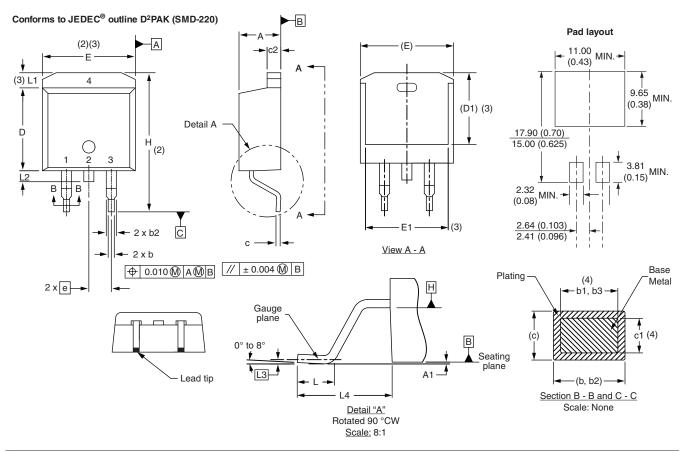
Outline Dimensions



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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES	NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	2.54 BSC 0.100 BSC			
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25 BSC 0.010 BSC) BSC		
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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